

MOSFET Silicon N-Channel MOS



1. Applications

Single-ended flyback or two-transistor forward topologies.
PC power, PD Adaptor, LCD & PDP TV and LED lighting.

2. Features

Low drain-source on-resistance: $R_{DS(ON)} = 620\text{m}\Omega$ (typ.)
Easy to control Gate switching
Enhancement mode: $V_{th} = 2.8$ to 4.2 V

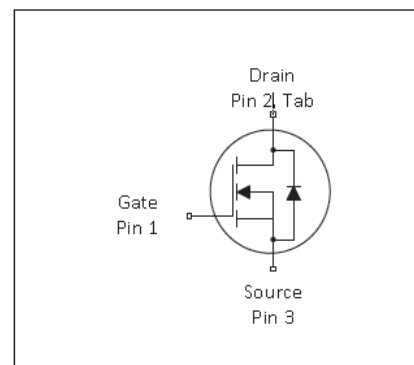
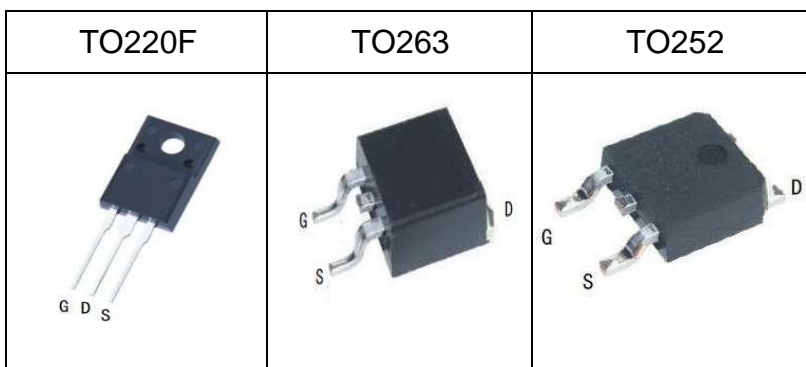


Table 1 Key Performance Parameters

Parameter	Value	Unit
$V_{DS} @ T_{j,max}$	850	V
$R_{DS(on),max}$	750	$\text{m}\Omega$
$Q_{g,typ}$	18.5	nC
$I_{D,pulse}$	35	A
Body diode dv/dt	50	V/ns

3. Packaging and Internal Circuit

Part Name	Package	Marking
ASA80R750E	TO220F	ASA80R750E
ASD80R750E	TO252	ASD80R750E
ASB80R750E	TO263	ASB80R750E



1 Maximum ratings

at $T_j = 25^\circ\text{C}$, unless otherwise specified

Table 2 Maximum ratings

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Continuous drain current ¹⁾	I_D		-	8.5	A	$T_C=25^\circ\text{C}$
Pulsed drain current ²⁾	$I_{D,pulse}$	-	-	35	A	$T_C=25^\circ\text{C}$
Avalanche energy, single pulse	E_{AS}	-	-	88	mJ	$T_C=25^\circ\text{C}, V_{DD}=50\text{V}, I_{av}=4.2\text{A}, L=10\text{mH}, R_G=25\Omega$
Avalanche current, single pulse	I_{AR}	-	-	4.2	A	$T_C=25^\circ\text{C}, V_{DD}=50\text{V}, L=10\text{mH}, R_G=25\Omega$
Gate source voltage (static)	V_{GS}	-30	-	30	V	static;
Power dissipation (TO220F)	P_{tot}	-	-	43	W	$T_C=25^\circ\text{C}$
Power dissipation (TO252&263)	P_{tot}	-	-	150	W	$T_C=25^\circ\text{C}$
Storage temperature	T_{stg}	-55	-	150	$^\circ\text{C}$	
Operating junction temperature	T_j	-55	-	150	$^\circ\text{C}$	
Soldering Temperature Distance of 1.6mm from case for 10s	T_L			260	$^\circ\text{C}$	
Reverse diode dv/dt ³⁾	dv/dt	-	-	4	V/ns	$V_{DS}=0\dots400\text{V}, I_{SD}\leq 8\text{A}, T_j=25^\circ\text{C}$ see table 8

¹⁾ Limited by $T_{j,max}$. Maximum Duty Cycle $D = 0.50$

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Identical low side and high side switch with identical R_G

2 Thermal characteristics

Thermal characteristics(TO220F)

Parameter	Symbol	Values			Unit	Note/Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction -case	R_{thJC}	-	-	3.26	°C/W	-
Thermal resistance, junction -ambient	R_{thJA}	-	-	76	°C/W	Device on PCB, minimal footprint

Thermal characteristics (TO252&263)

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Thermal resistance, junction - case	R_{thJC}	-	-	1.1	°C/W	-
Thermal resistance, junction - ambient	R_{thJA}	-	-	62	°C/W	device on PCB, minimal footprint

3 Electrical characteristics

at $T_j=25^{\circ}\text{C}$, unless otherwise specified

Table 4 Static characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Drain-source breakdown voltage	$V_{(BR)DSS}$	800	-	-	V	$V_{GS}=0V, I_D=250\mu A$
Gate threshold voltage	$V_{(GS)th}$	2.8		4.2	V	$V_{DS}=V_{GS}, I_D=250\mu A$
Zero gate voltage drain current	I_{DSS}	-	-	1	μA	$V_{DS}=800V, V_{GS}=0V, T_j=25^{\circ}\text{C}$
Gate-source leakage current	I_{GSS}	-	-	100	nA	$V_{GS}=30V, V_{DS}=0V$
Drain-source on-state resistance	$R_{DS(on)}$	-	620	750	m Ω	$V_{GS}=10V, I_D=6A, T_j=25^{\circ}\text{C}$
Gate resistance (Intrinsic)	R_G	-	25	-	Ω	$f=1\text{MHz}$, open drain

Table 5 Dynamic characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Input capacitance	C_{iss}	-	850.8	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Output capacitance	C_{oss}	-	34.4	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Reverse transfer capacitance	C_{rss}	-	0.92	-	pF	$V_{GS}=0V, V_{DS}=100V, f=1\text{MHz}$
Turn-on delay time	$t_{d(on)}$	-	40.6	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=4.1A, R_G=50\Omega$
Rise time	t_r	-	34.8	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=4.1A, R_G=50\Omega$
Turn-off delay time	$t_{d(off)}$	-	128	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=4.1A, R_G=50\Omega$
Fall time	t_f	-	31	-	ns	$V_{DD}=400V, V_{GS}=10V, I_D=4.1A, R_G=50\Omega$

Table 6 Gate charge characteristics

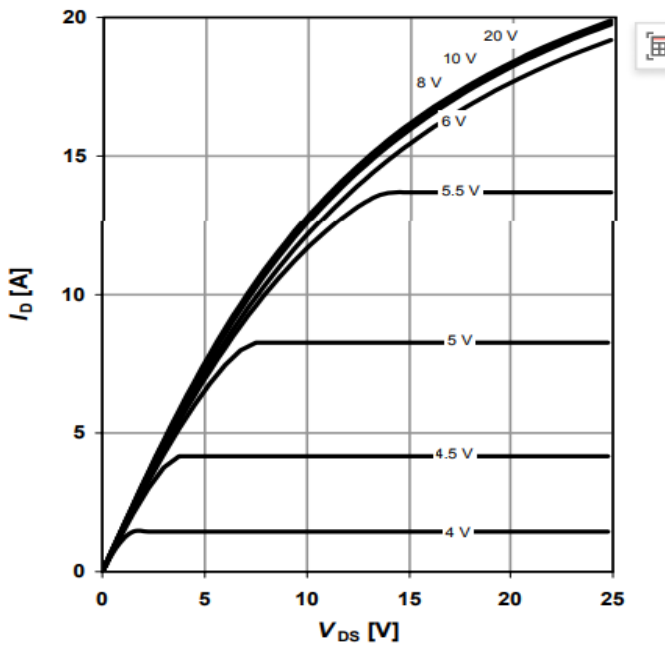
Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Gate to source charge	Q_{gs}	-	5.0	-	nC	$V_{DD}=400V, I_D=4.1A, V_{GS}=0$ to 10V
Gate to drain charge	Q_{gd}	-	6.6	-	nC	$V_{DD}=400V, I_D=4.1A, V_{GS}=0$ to 10V
Gate charge total	Q_g	-	18.5	-	nC	$V_{DD}=400V, I_D=4.1A, V_{GS}=0$ to 10V

Table 7 Reverse diode characteristics

Parameter	Symbol	Values			Unit	Note / Test Condition
		Min.	Typ.	Max.		
Diode forward voltage	V_{SD}	-	0.75	-	V	$V_{GS}=0V, I_F=1A, T_J=25^{\circ}C$
Reverse recovery time	t_{rr}	-	266.5	-	ns	$V_R=400V, I_F=4.1A, di_F/dt=100A/\mu s$
Reverse recovery charge	Q_{rr}	-	2.2	-	μC	$V_R=400V, I_F=4.1A, di_F/dt=100A/\mu s$
Peak reverse recovery current	I_{rrm}	-	14	-	A	$V_R=400V, I_F=4.1A, di_F/dt=100A/\mu s$

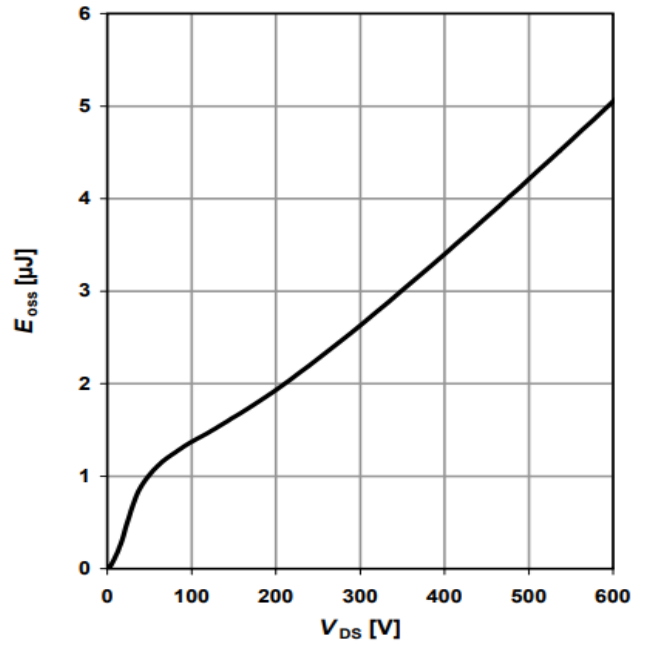
4 Electrical characteristics diagram

Diagram 1: Typ. output characteristics



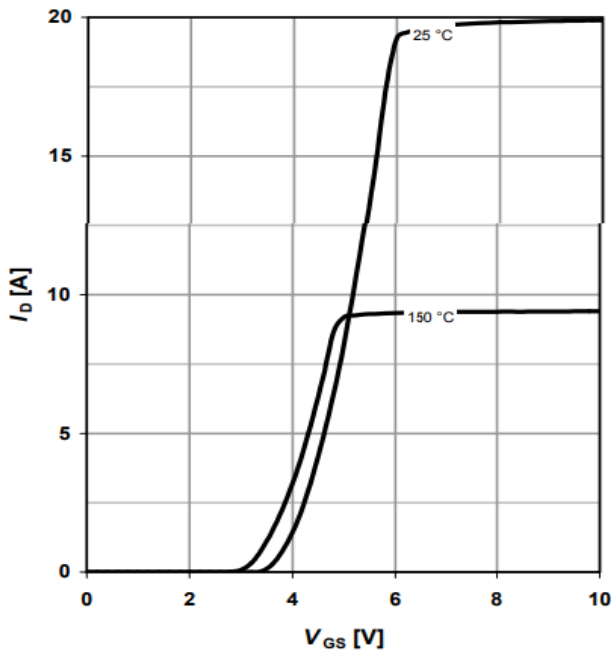
$I_D=f(V_{DS}); T_j=25\text{ }^\circ\text{C};$ parameter: V_{GS}

Diagram 2: Typ. Coss stored energy



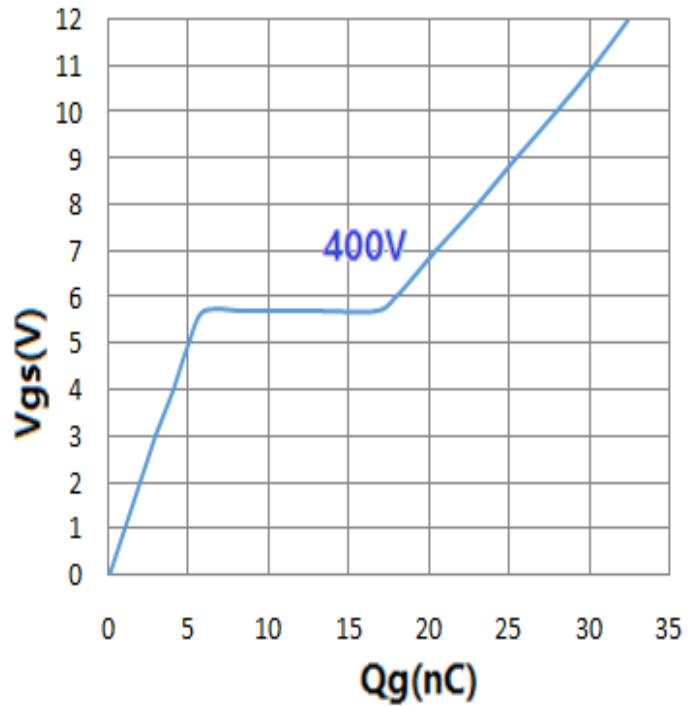
$E_{oss}=f(V_{DS})$

Diagram 3: Typ. transfer characteristics



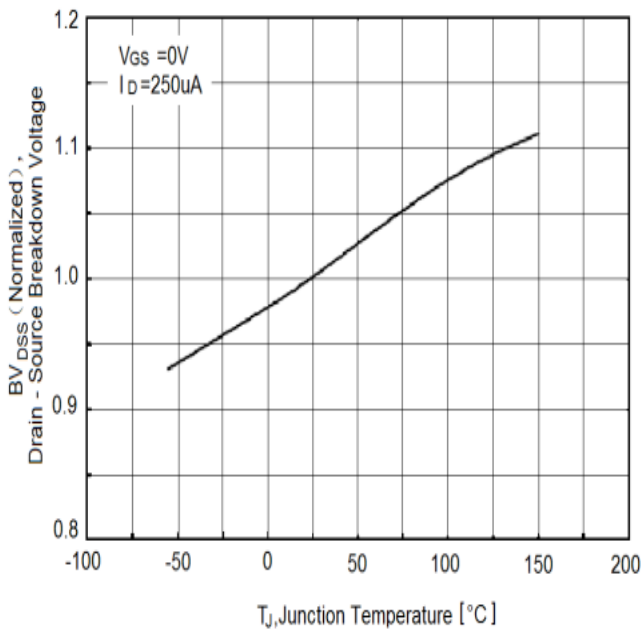
$I_D=f(V_{GS});$ parameter: T_j

Diagram 4: Typ. gate charge



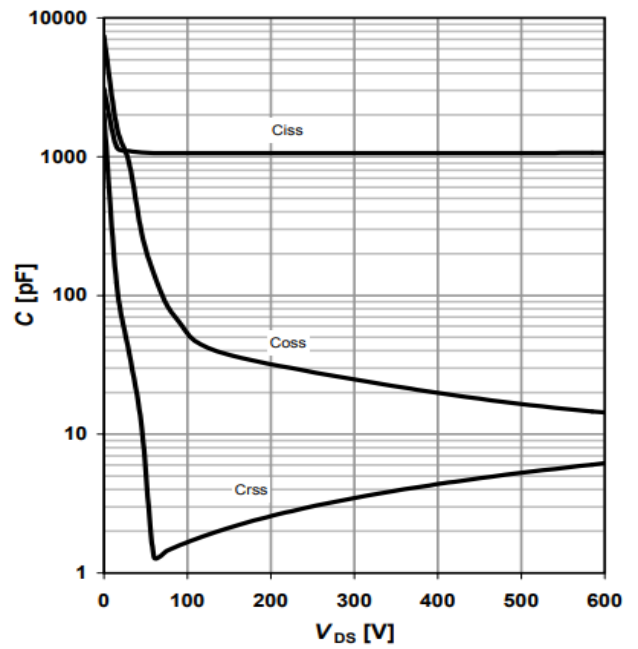
$V_{GS}=f(Q_{gate}); I_D=4.1\text{A pulsed};$ parameter: V_{DD}

Diagram 5: Drain-source breakdown voltage



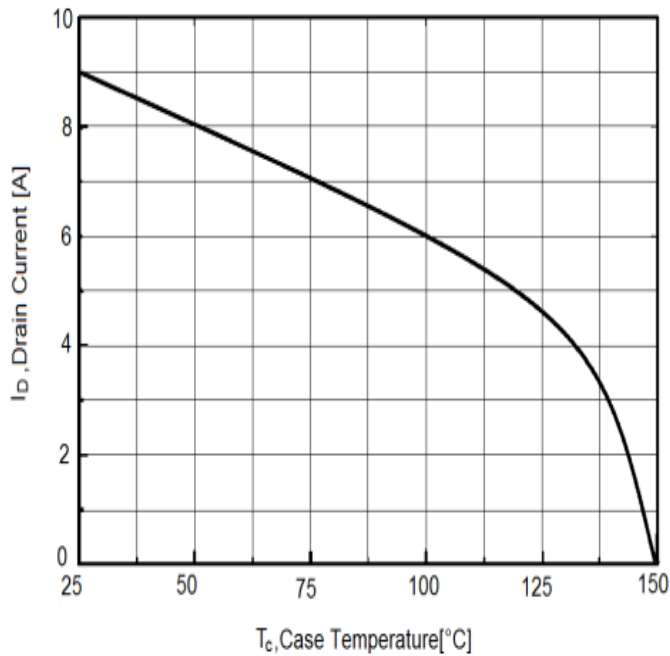
$V_{BR(DSS)} = f(T_j); I_D = 250\mu A$

Diagram 6: Typ. capacitances



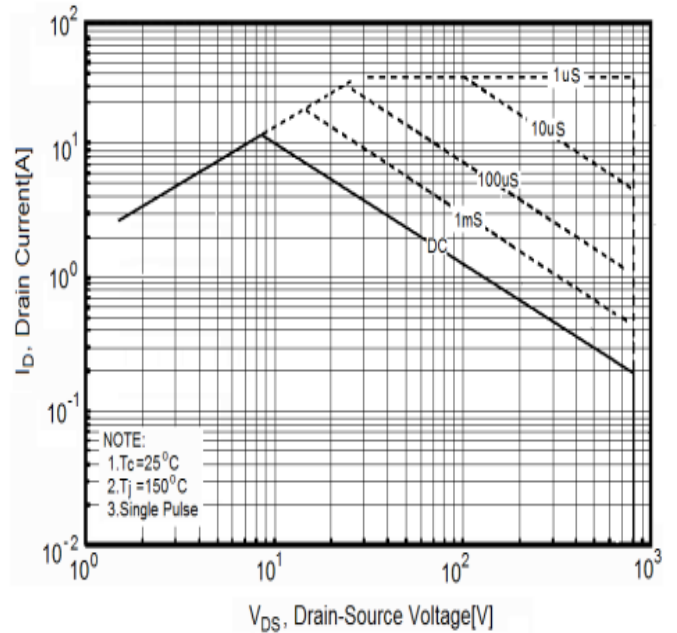
$C = f(V_{DS}); V_{GS} = 0V; f = 10 \text{ kHz}$

Diagram 7: Maximum id vs Junction Temperature



$V_{BR(DSS)} = f(T_j); I_D = 250\mu A$

Diagram 8: Safe Operating Area



$C = f(V_{DS}); V_{GS} = 0V; f = 10 \text{ kHz}$

5 Test Circuits

Table 8 Diode characteristics

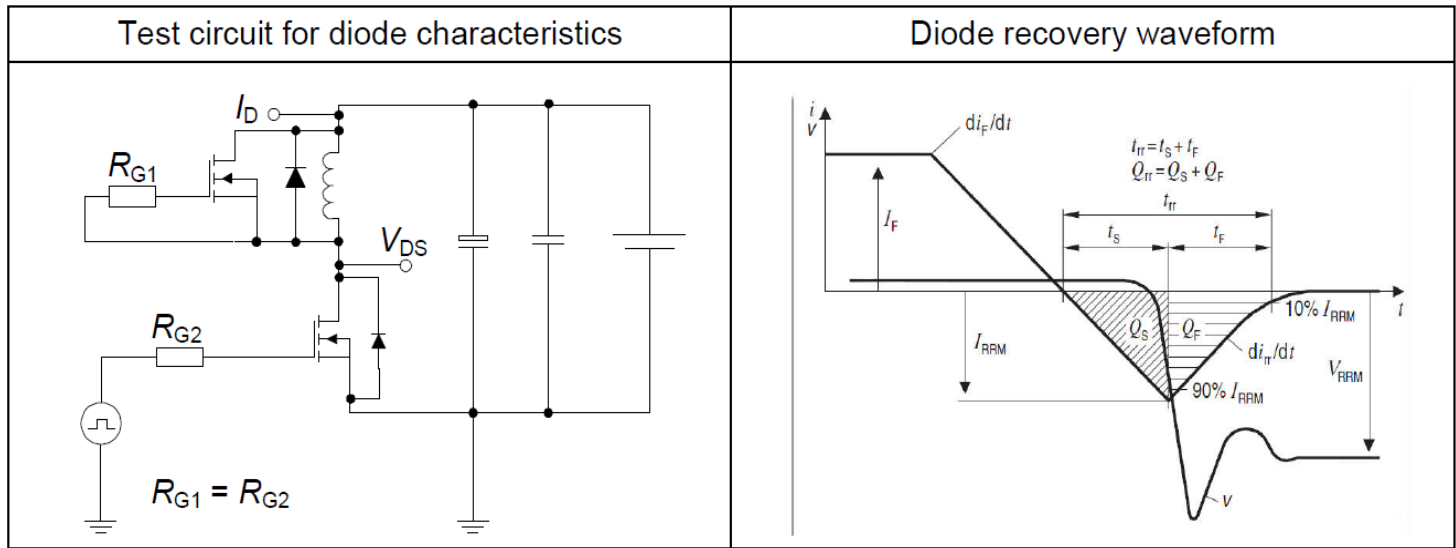


Table 9 Switching times

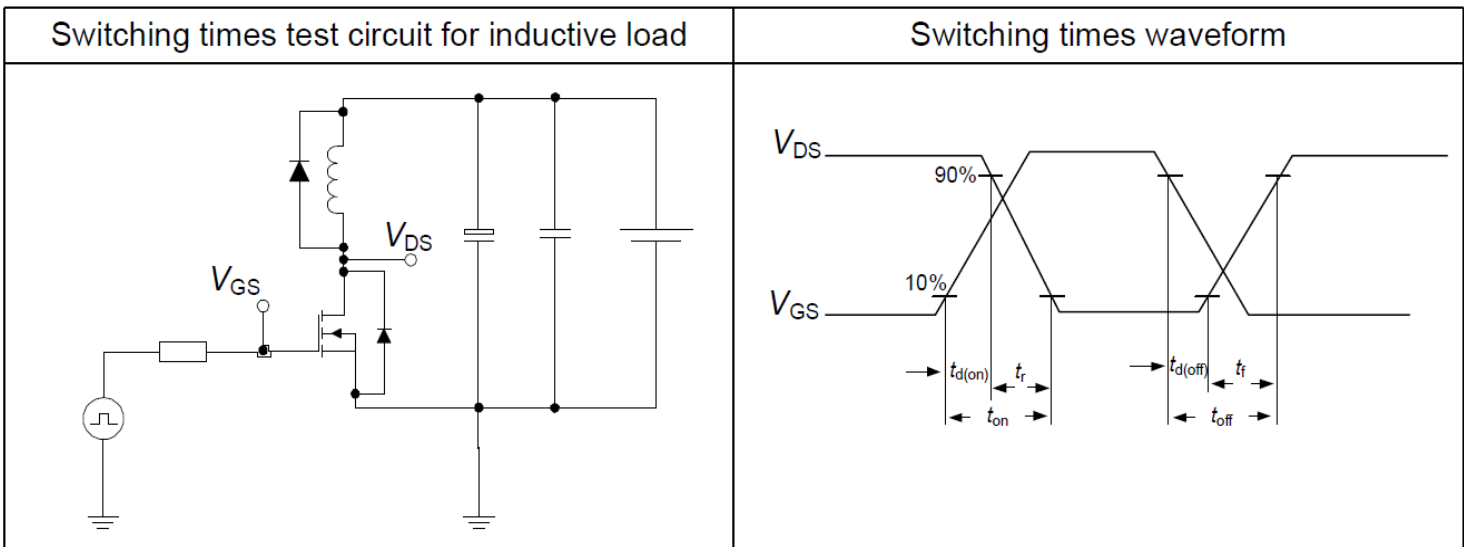
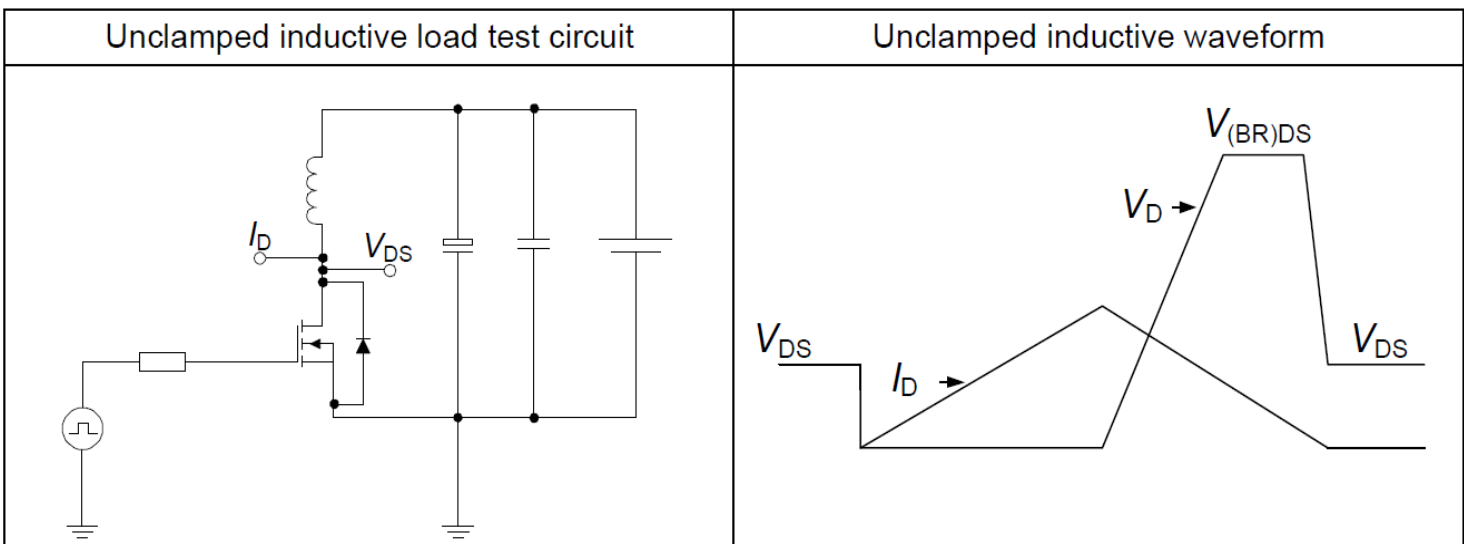
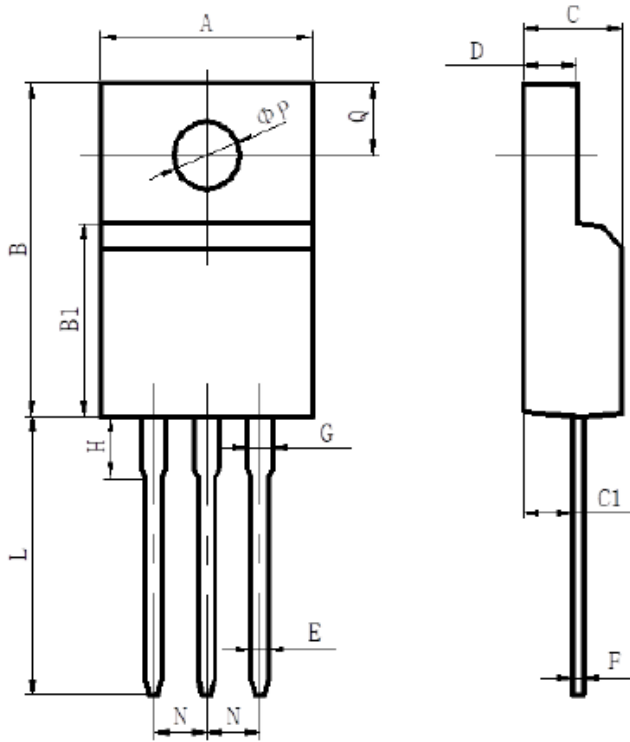


Table 10 Unclamped inductive load

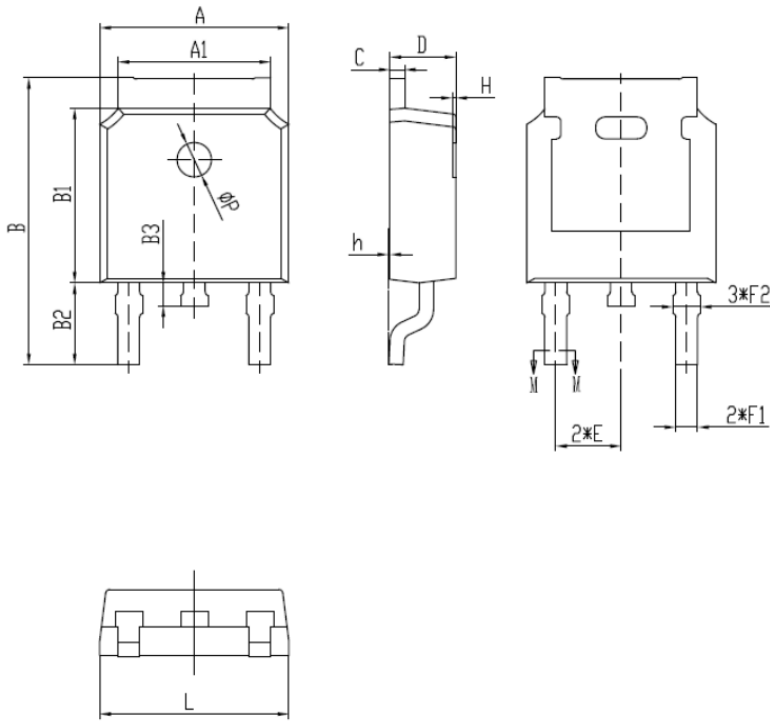


6 Package Outlines



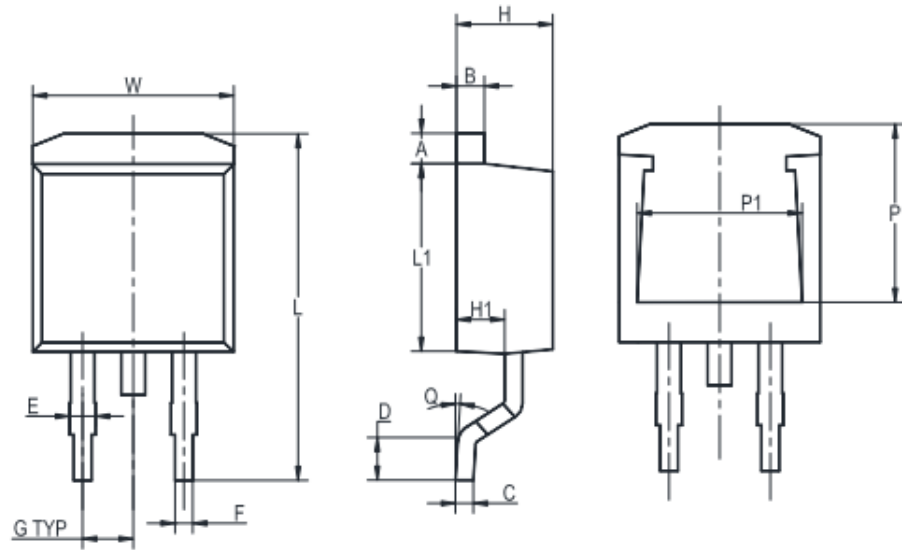
项目	规范(mm)	
	MIN	MAX
A	9.70	10.30
B	15.50	16.10
B1	8.99	9.39
C	4.40	4.80
C1	2.15	2.55
D	2.50	2.90
E	0.70	0.90
F	0.40	0.60
G	1.12	1.42
H	3.40	3.80
L	12.6	13.6
N	2.34	2.74
Q	3.15	3.55
ϕP	3.00	3.30

Figure 1: Outline PG-TO220F(HT)



项目	规范(mm)	
	MIN	MAX
A	6.50	6.70
A1	5.16	5.46
B	9.77	10.17
B1	6.00	6.20
B2	2.60	3.00
B3	0.70	0.90
C	0.45	0.61
D	2.20	2.40
E	2.186	2.386
F1	0.67	0.87
F2	0.76	0.96
H	0.00	0.30
h	0.00	0.127
L	6.50	6.70
ϕP	1.10	1.30

Figure 2: Outline PG-T0252(HT)



UNIT	A	B	C	D	E	F	G	W	H	H1	L	L1	Q	P	P1
mm	1.5	1.5	0.5	2.60	1.6	0.94	2.54	10.5	4.8	2.9	16.5	8.7	8°	7.6	8.2
	1.1	1.1	0.3	2.15	1.1	0.68	TYP	9.6	4.4	2.5	14.5	8.2	MAX	7.1	7.4

Figure 3: Outline PG-T0263(HC&LM)

Revision History

Revision	Date	Subjects (major changes since last revision)
1.0	2021-11-29	Preliminary version
1.1	2022-07-29	Added TO252 package
1.2	2023-06-02	Added TO263 package

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